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## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



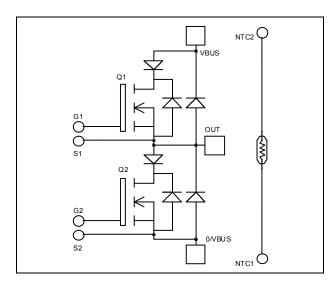


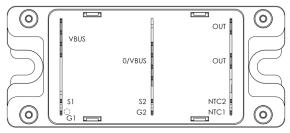




# Phase leg Series & parallel diodes MOSFET Power Module

$$\begin{split} V_{DSS} &= 500V \\ R_{DSon} &= 38 m \Omega \text{ typ } @ \text{ Tj} = 25^{\circ} C \\ I_D &= 90 A @ \text{ Tc} = 25^{\circ} C \end{split}$$





#### **Application**

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

#### **Features**

- Power MOS 7<sup>®</sup> MOSFETs
  - Low R<sub>DSon</sub>
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

## All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		500	V
T	(Confinitoric Drain Current	$T_c = 25^{\circ}C$	90	
$I_{D}$		$T_c = 80$ °C	67	A
$I_{DM}$	Pulsed Drain current		360	
$V_{GS}$	Gate - Source Voltage		±30	V
R <sub>DSon</sub>	Drain - Source ON Resistance		45	mΩ
$P_{D}$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	694	W
$I_{AR}$	Avalanche current (repetitive and non repetitive)		46	A
$E_{AR}$	Repetitive Avalanche Energy	50		m.J
$E_{AS}$	Single Pulse Avalanche Energy		2500	IIIJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$ $T_j = 25^{\circ}C$			200	4
		$V_{GS} = 0V, V_{DS} = 400V$ $T_j = 125^{\circ}C$			1000	μΑ
R <sub>DS(on)</sub>	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 45A$		38	45	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$	3		5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±200	nA

**Dynamic Characteristics** 

•	Characteristic	Test Conditions	Min	Typ	Max	Unit
C <sub>iss</sub>	Input Capacitance	$V_{GS} = 0V$	171010	11.2	1711111	Omi
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		2.4		nF
$C_{rss}$	Reverse Transfer Capacitance	f = 1MHz		0.18		
$Q_{\mathrm{g}}$	Total gate Charge	$V_{GS} = 10V$		246		
$Q_{\rm gs}$	Gate – Source Charge	$V_{\text{Bus}} = 250 \text{V}$		66		nC
$Q_{\mathrm{gd}}$	Gate – Drain Charge	$I_D = 90A$		130		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		18		
$T_{\rm r}$	Rise Time	$V_{GS} = 15V$		35		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{\text{Bus}} = 333V$ $I_{\text{D}} = 90A$		87		
$T_{\mathrm{f}}$	Fall Time	$R_G = 2\Omega$		77		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		1510		
$E_{\text{off}}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 90A, R_G = 2\Omega$		1452		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		2482		
E <sub>off</sub>	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 90A, R_G = 2\Omega$		1692		μJ
$R_{thJC}$	Junction to Case Thermal Resistance				0.18	°C/W

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R=600V$				250	μA
$I_{\mathrm{F}}$	DC Forward Current		$T_c = 80^{\circ}C$		90		Α
	Diode Forward Voltage	$I_F = 90A$			1.6	1.8	
$V_{\mathrm{F}}$		$I_{\rm F} = 180A$			1.9		V
		$I_F = 90A$	$T_{j} = 125^{\circ}C$		1.4		
+	Reverse Recovery Time		$T_j = 25$ °C		85		na
t <sub>rr</sub>		$I_F = 90A$ $V_R = 400V$	$T_{j} = 125^{\circ}C$		160		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$di/dt = 600A/\mu s$	$T_j = 25^{\circ}C$		390		пC
			$T_j = 125$ °C		2100		iiC
$R_{thJC}$	Junction to Case Thermal Resistance					0.45	°C/W



Parallel diode ratings and characteristics

Symbol	Characteristic	haracteristic Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_{R} = 600V$				250	μA
$I_{\mathrm{F}}$	DC Forward Current		$T_c = 90$ °C		90		A
	Diode Forward Voltage	$I_{\rm F} = 90A$			1.8	2.2	
$V_{\mathrm{F}}$		$I_{\rm F} = 180A$			2		V
		$I_F = 90A$	$T_{j} = 125^{\circ}C$		1.3		
_	Reverse Recovery Time		$T_j = 25$ °C		25		
$t_{rr}$		$I_F = 90A$ $V_R = 400V$	$T_j = 125$ °C		160		ns
Qrr	Reverse Recovery Charge	$di/dt = 600 \text{A/}\mu\text{s}$	$T_j = 25^{\circ}C$		105		nC
		$T_{\rm j}$	$T_j = 125^{\circ}C$		1440		IIC
$R_{\text{thJC}}$	Junction to Case Thermal Resistance					0.45	°C/W

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
$T_{J}$	Operating junction temperature range			-40	150	
$T_{JOP}$	Recommended junction temperature under switching conditions			-40	T <sub>J</sub> max -25	°C
$T_{STG}$	Storage Temperature Range			-40	125	C
$T_{\rm C}$	Operating Case Temperature			-40	100	
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

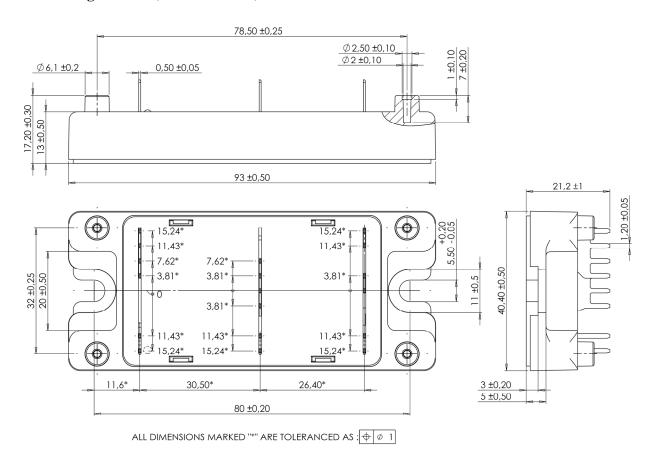
Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		$T_{\rm C} = 100^{\circ}{\rm C}$		4		%

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{-1}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R<sub>T</sub>: Thermistor value at T



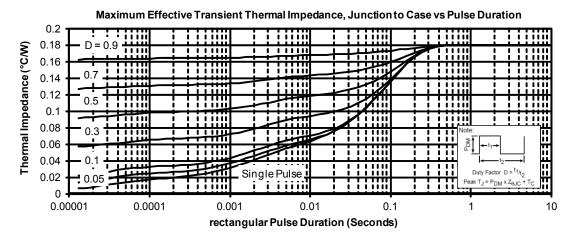
## SP4 Package outline (dimensions in mm)

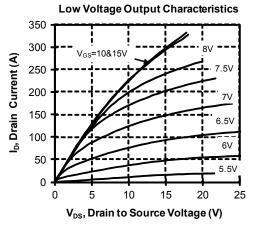


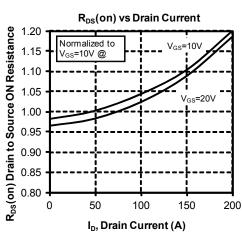
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

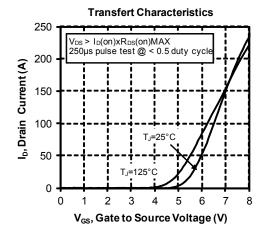


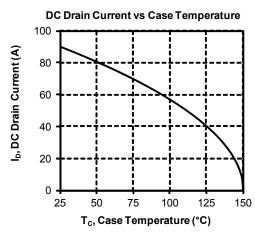
## **Typical Performance Curve**



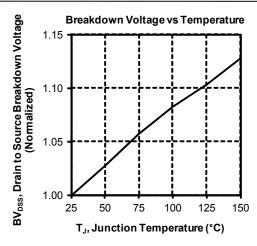


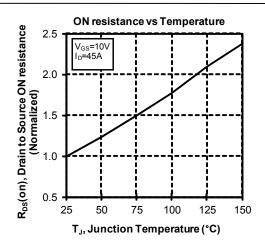


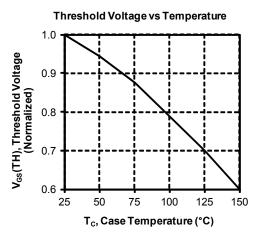


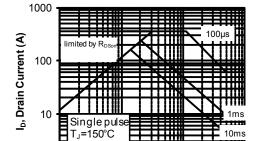












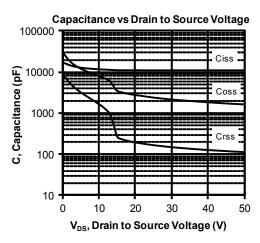
c=25°C

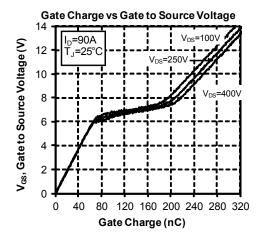
Maximum Safe Operating Area



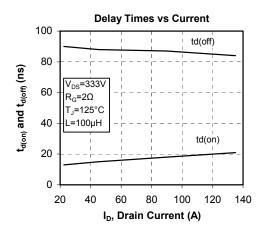
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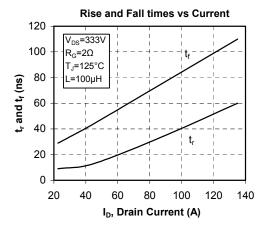
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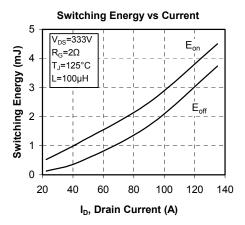


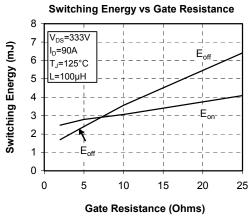


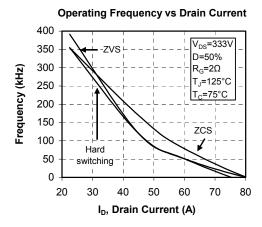


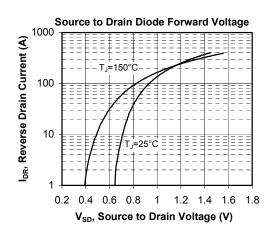












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